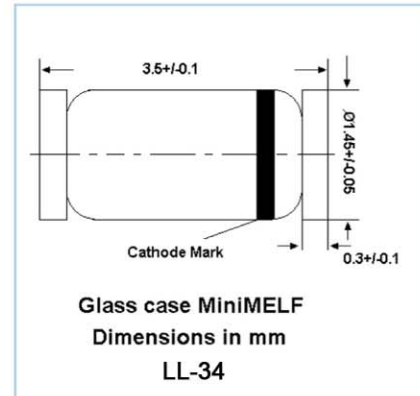


## Silicon Schottky Barrier Diode

Characteristics equivalent to or better than 1N60P  
ideal for used in detection or for switching on the  
radio, TV, etc.

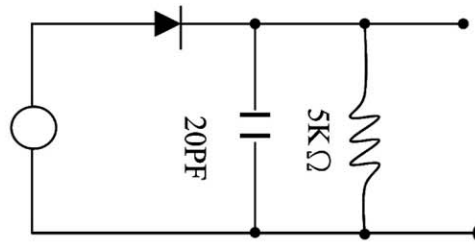


### Absolute Maximum Ratings ( $T_a = 25^\circ\text{C}$ )

Parameter	Symbol	Value	Unit
Peak Reverse Voltage	$V_{RM}$	45	V
Reverse Voltage	$V_R$	20	V
Average Rectified Output Current	$I_O$	50	mA
Peak Forward Current	$I_{FM}$	150	mA
Surge Forward Current	$I_{surge}$	500	mA
Junction Temperature	$T_j$	125	$^\circ\text{C}$
Storage Temperature Range	$T_{stg}$	- 55 to + 150	$^\circ\text{C}$

### Characteristics at $T_a = 25^\circ\text{C}$

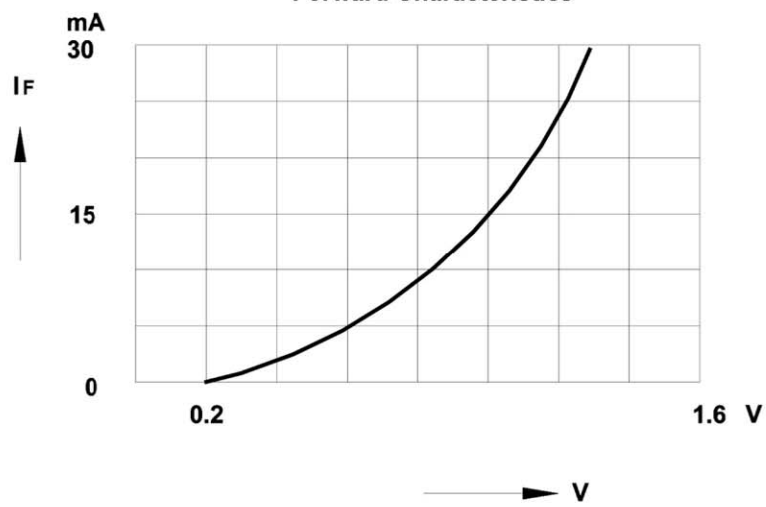
Parameter	Symbol	Min.	Max.	Unit
Forward Current at $V_F = 1\text{ V}$	$I_F$	4	-	mA
Reverse Current at $V_R = 10\text{ V}$	$I_R$	-	50	$\mu\text{A}$
Total Capacitance At $V = -1\text{ V}$ , $f = 1\text{ MHz}$	$C_{tot}$	-	1	pF
Rectification efficiency at $V_i = 2\text{ V}_{rms}$ , $R = 5\text{ K}\Omega$	$\eta$	55	-	%



Input 2Vrms

Rectification Efficiency Measurement Circuit

Forward Characteristics



Reverse Characteristics

